

ON Semiconductor

Is Now



To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and onsemi. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.



ON Semiconductor®

FCB20N60-F085

N-Channel MOSFET

600V, 20A, 198mΩ

Features

- Typ $r_{DS(on)}$ = 173mΩ at V_{GS} = 10V, I_D = 20A
- Typ $Q_{g(tot)}$ = 72nC at V_{GS} = 10V, I_D = 20A
- UIS Capability
- RoHS Compliant
- Qualified to AEC Q101

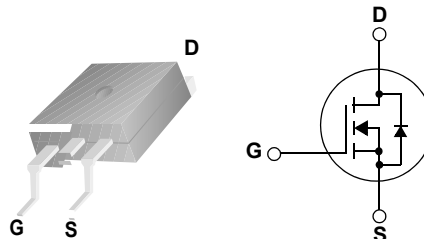
Description

SuperFET™ is ON Semiconductor's proprietary new generation of high voltage MOSFETs utilizing an advanced charge balance mechanism for outstanding low on-resistance and

lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy.

Consequently, SuperFET is suitable for various automotive DC/DC power conversion.



Applications

- Automotive On Board Charger
- Automotive DC/DC converter for HEV

MOSFET Maximum Ratings $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	600	V
V_{GS}	Gate to Source Voltage	±30	V
I_D	Drain Current - Continuous ($V_{GS}=10$) (Note 1)	$T_C = 25^\circ\text{C}$	A
	Pulsed Drain Current	$T_C = 25^\circ\text{C}$	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	480	mJ
P_D	Power Dissipation	341	W
	Derate above 25°C	2.3	W/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to + 150	°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	0.44	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance Junction to Ambient (Note 3)	43	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCB20N60	FCB20N60-F085	TO-263AB	330mm	24mm	800 units

Notes:

1: Current is limited by bondwire configuration.

2: Starting $T_J = 25^\circ\text{C}$, $L = 15\text{mH}$, $I_{AS} = 8\text{A}$, $V_{DD} = 100\text{V}$ during inductor charging and $V_{DD} = 0\text{V}$ during time in avalanche

3: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	600	-	-	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS} = 600\text{V}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{V}$, $T_J = 150^\circ\text{C}(\text{Note } 4)$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 30\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	3.0	4.0	5.0	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 20\text{A}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 10\text{V}$, $T_J = 150^\circ\text{C}(\text{Note } 4)$	-	173	198	$\text{m}\Omega$
			-	471	570	$\text{m}\Omega$

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		-	2710	3080	pF
C _{oss}	Output Capacitance			-	1350	1665	pF
C _{rss}	Reverse Transfer Capacitance			-	86	150	pF
R _g	Gate Resistance	f = 1MHz		-	1	-	Ω
Q _{g(ToT)}	Total Gate Charge at 10V	V _{GS} = 0 to 10V	V _{DD} = 300V I _D = 20A	-	72	102	nC
Q _{g(th)}	Threshold Gate Charge	V _{GS} = 0 to 2V		-	5	8.6	nC
Q _{gs}	Gate to Source Gate Charge			-	15	-	nC
Q _{gd}	Gate to Drain “Miller” Charge			-	31	-	nC

Switching Characteristics

t_{on}	Turn-On Time	$V_{DD} = 300\text{V}$, $I_D = 20\text{A}$, $V_{GS} = 10\text{V}$, $R_G = 25\Omega$	-	-	166	ns
$t_{d(on)}$	Turn-On Delay Time		-	44	-	ns
t_r	Rise Time		-	60	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	208	-	ns
t_f	Fall Time		-	43	-	ns
t_{off}	Turn-Off Time		-	-	400	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 20\text{A}$, $V_{GS} = 0\text{V}$	-	-	1.4	V
T_{rr}	Reverse Recovery Time	$I_F = 20\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	486	632	ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 480\text{V}$	-	10	13	μC

Notes:

4: The maximum value is specified by design at $T_J = 150^\circ\text{C}$. Product is not tested to this condition in production.

Typical Characteristics

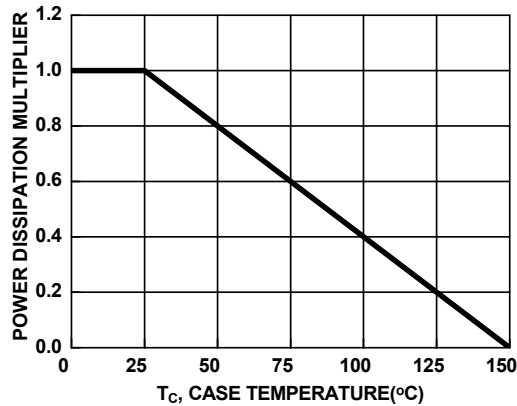


Figure 1. Normalized Power Dissipation vs Case Temperature

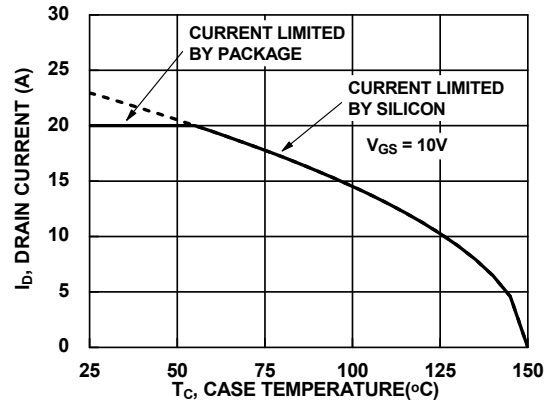


Figure 2. Maximum Continuous Drain Current vs Case Temperature

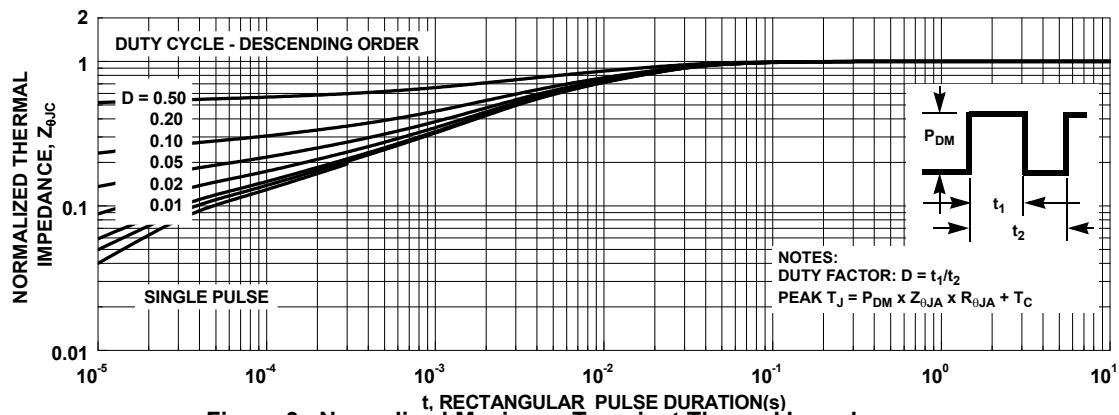


Figure 3. Normalized Maximum Transient Thermal Impedance

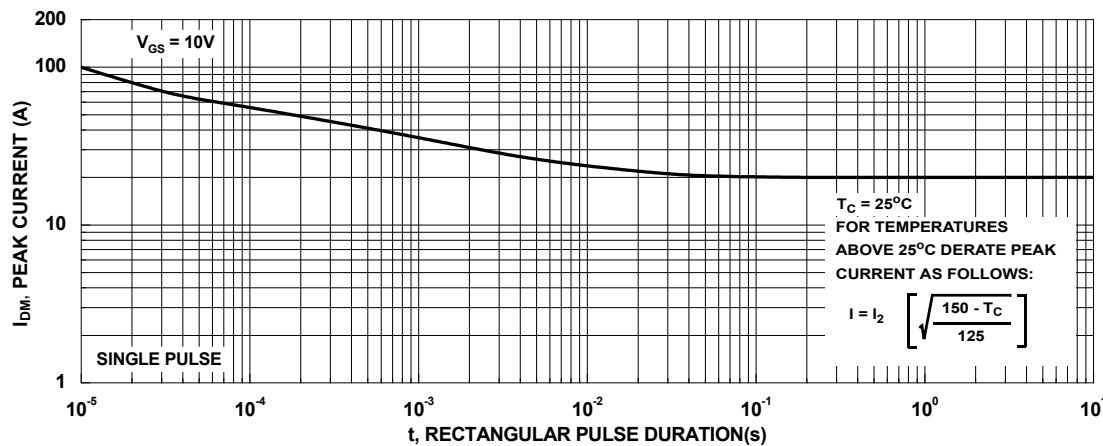


Figure 4. Peak Current Capability

Typical Characteristics

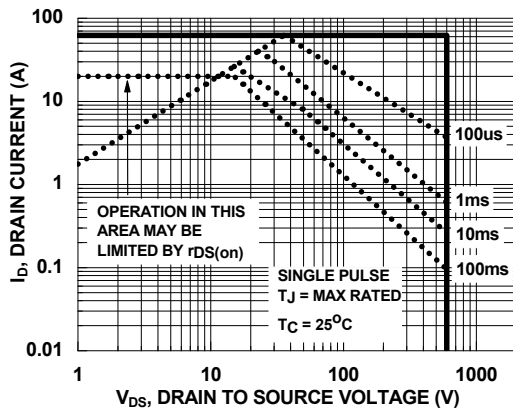


Figure 5. Forward Bias Safe Operating Area

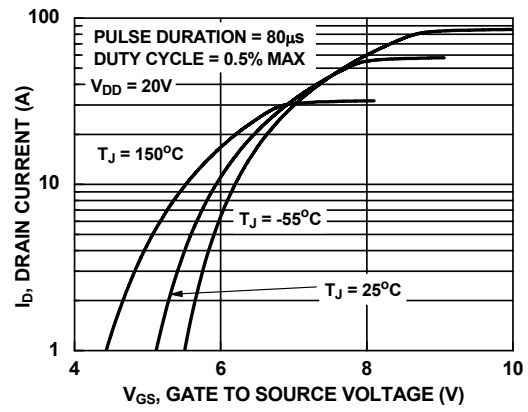


Figure 6. Transfer Characteristics

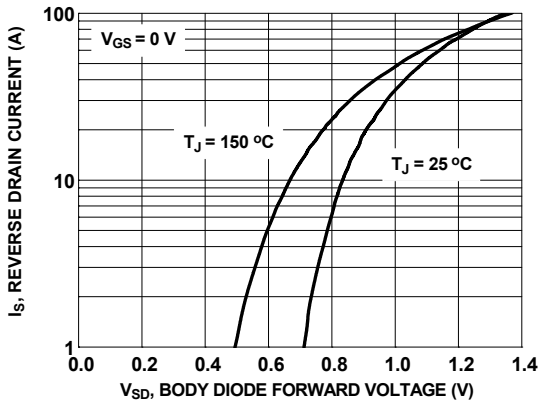


Figure 7. Forward Diode Characteristics

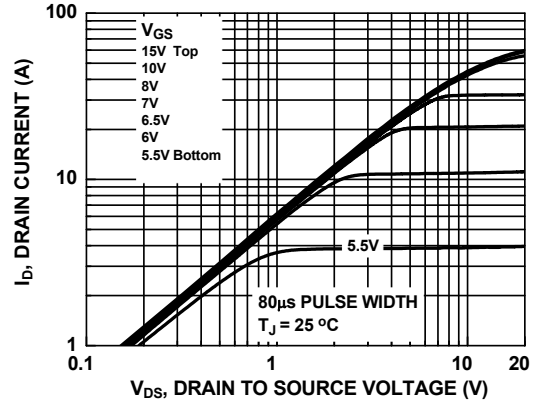


Figure 8. Saturation Characteristics

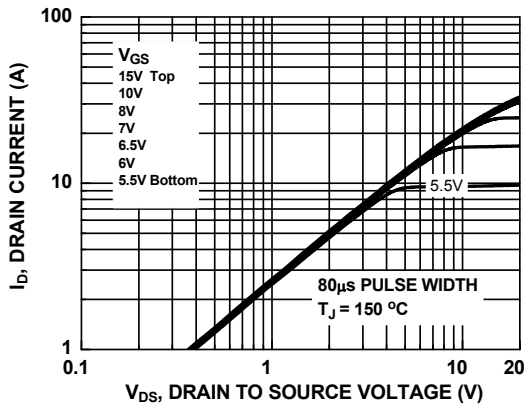


Figure 9. Saturation Characteristics

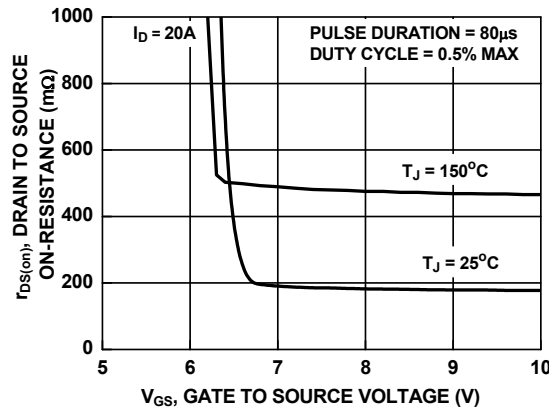


Figure 10. Rdson vs Gate Voltage

Typical Characteristics

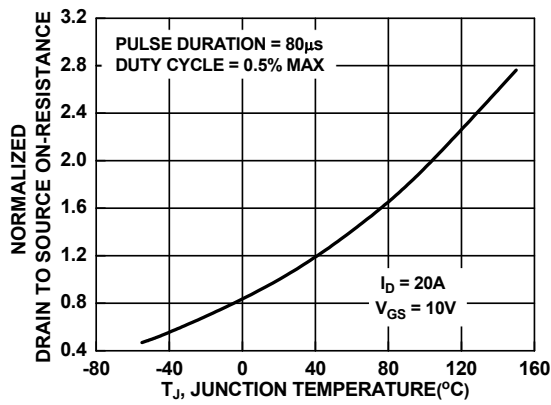


Figure 11. Normalized $R_{ds(on)}$ vs Junction Temperature

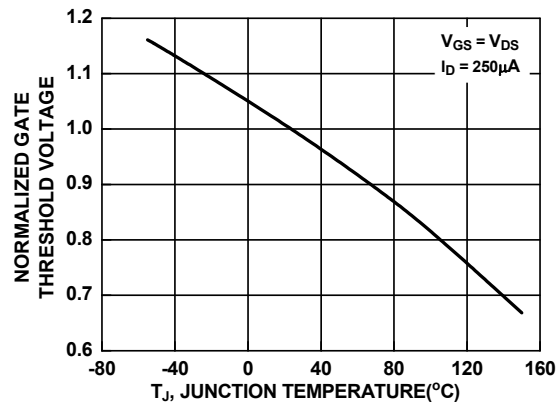


Figure 12. Normalized Gate Threshold Voltage vs Temperature

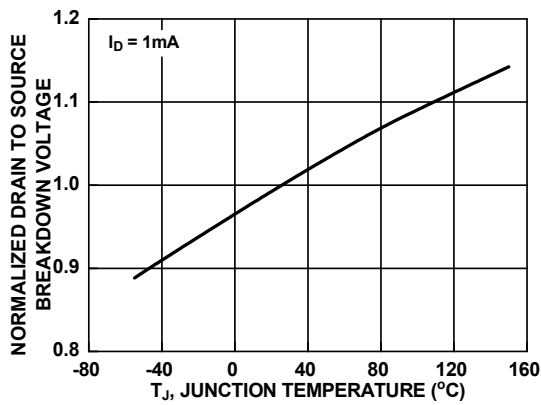


Figure 13. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

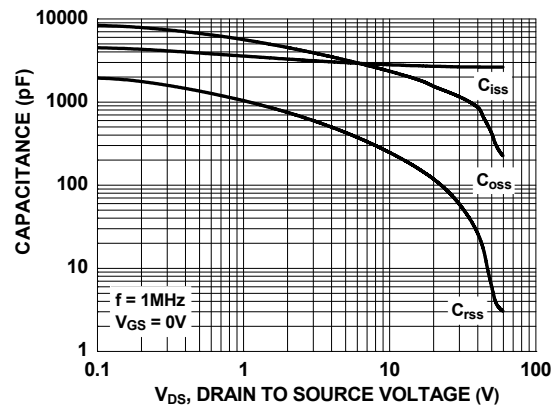


Figure 14. Capacitance vs Drain to Source Voltage

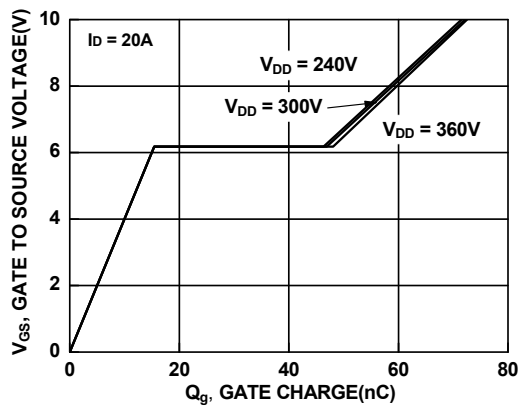


Figure 15. Gate Charge vs Gate to Source Voltage

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[onsemi:](#)

[FCB20N60-F085](#)